



**THE DATASHEET OF
1SS244T-72**



Switching diode

1SS244

●Applications

High voltage switching
General purpose rectification

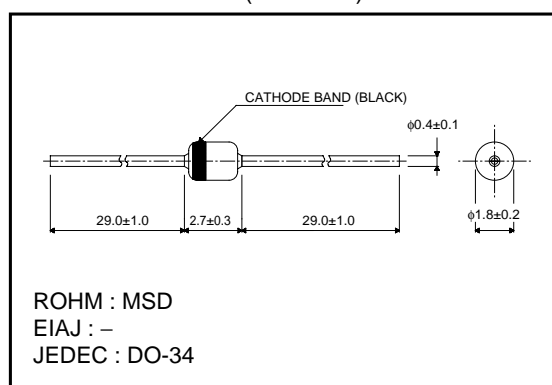
●Features

- 1) Glass sealed envelope. (MSD)
- 2) $V_{RM}=250V$ guaranteed.
- 3) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	250	V
DC reverse voltage	V_R	220	V
Peak forward current	I_{FM}	625	mA
Mean rectifying current	I_o	200	mA
Surge current (1s)	I_{surge}	1000	mA
Power dissipation	P	300	mW
Junction temperature	T_j	175	$^\circ\text{C}$
Storage temperature	T_{stg}	-65~+175	$^\circ\text{C}$

●Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	1.5	V	$I_F=200\text{mA}$
Reverse current	I_R	-	-	10	μA	$V_R=220\text{V}$
Capacitance between terminals	C_T	-	-	3	pF	$V_R=0\text{V}$, $f=1\text{MHz}$
Reverse recovery time	t_{rr}	-	-	75	ns	$I_F=20\text{mA}$, $I_R=20\text{mA}$, $R_L=50\Omega$

Diodes

●Electrical characteristics curves (Ta=25°C)

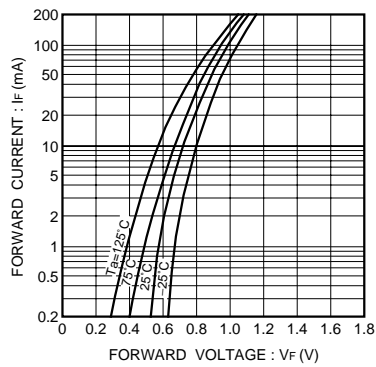


Fig.1 Forward characteristics

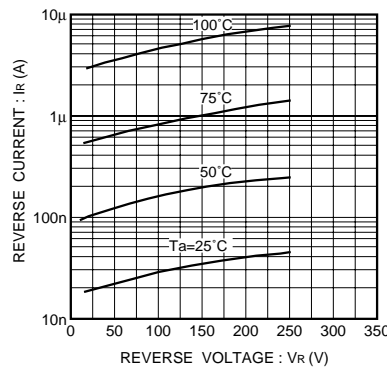


Fig.2 Reverse characteristics

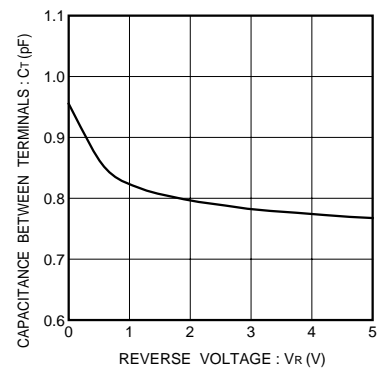


Fig.3 Capacitance between terminals characteristics

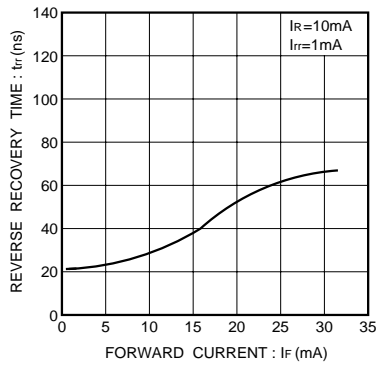


Fig.4 Reverse recovery time characteristics

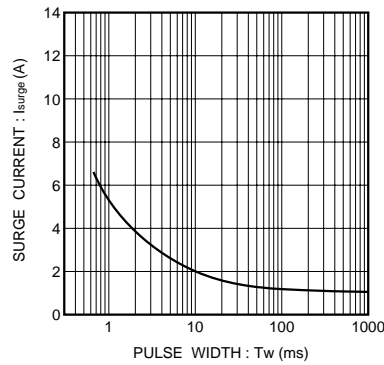


Fig.5 Surge current characteristics

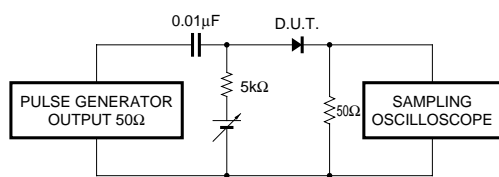


Fig.6 Reverse recovery time (trr) measurement circuit

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